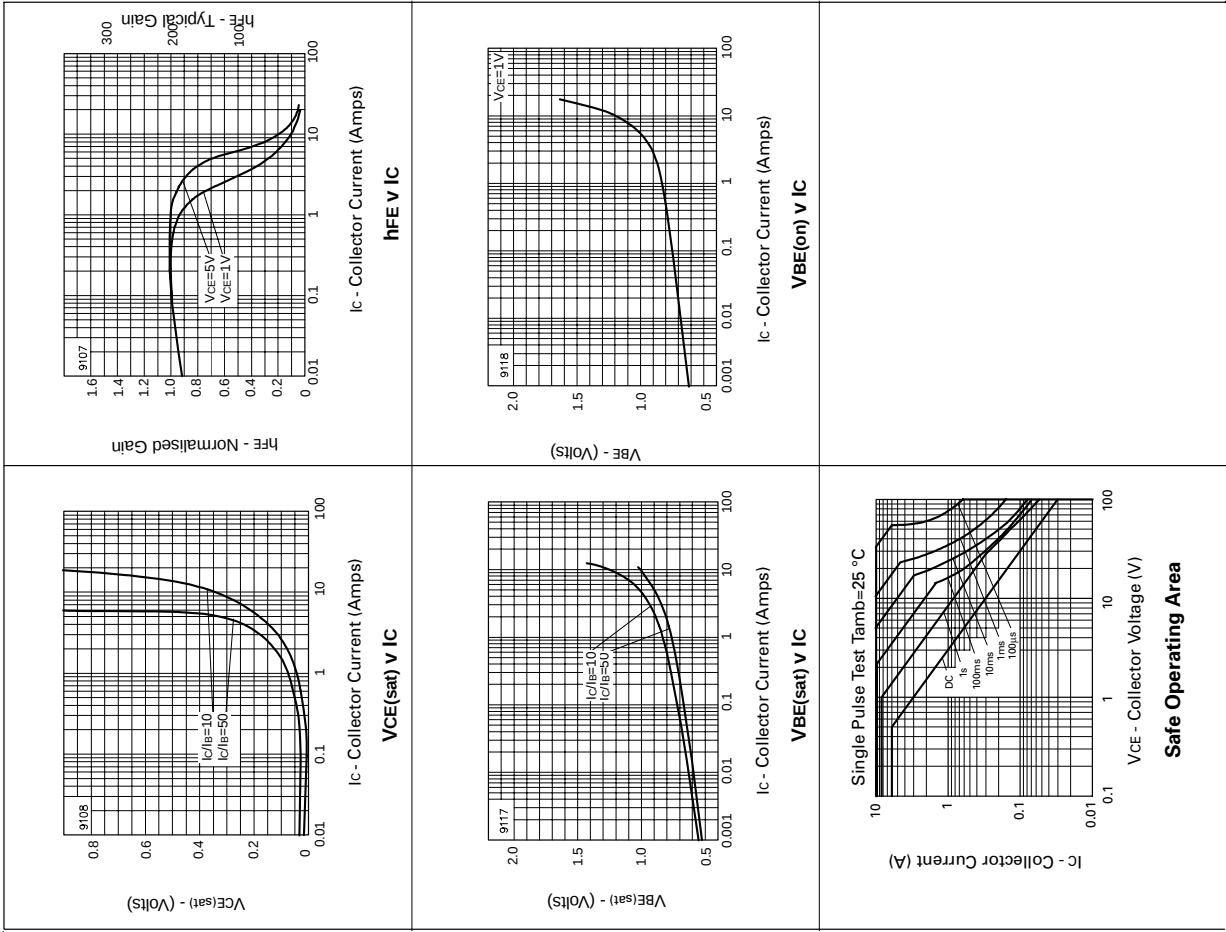


ELECTRICAL CHARACTERISTICS $T_{amb} = 25^{\circ}C$ (atunless otherwise stated)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	200	300		V	$I_C=100\mu A$
Collector-Emitter Breakdown Voltage	$V_{(BR)CER}$	200	300		V	$I_C=1\mu A, R_B \leq 1k\Omega$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	100	120		V	$I_C=10mA^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	6	8		V	$I_E=100\mu A$
Collector Cut-Off Current	I_{CBO}			10 1	nA μA	$V_{CB}=150V, T_{amb}=25^{\circ}C$ $V_{CB}=150V$ $T_{amb}=100^{\circ}C$
Collector Cut-Off Current	I_{CER} $R \leq 1k\Omega$			10 1	nA μA	$V_{CB}=150V, T_{amb}=25^{\circ}C$ $V_{CB}=150V$ $T_{amb}=100^{\circ}C$
Emitter Cut-Off Current	I_{EBO}			10	nA	$V_{EB}=6V$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		14 100	50 150 340	mV mV mV	$I_C=0.1A, I_B=5mA^*$ $I_C=2A, I_B=100mA^*$ $I_C=5A, I_B=500mA^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			1250	mV	$I_C=5A, I_B=500mA^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$			1100	mV	$I_C=5A, V_{CE}=2V^*$
Static Forward Current Transfer Ratio	h_{FE}	100 100 50 20	200 200 100 30	300		$I_C=10mA, V_{CE}=2V$ $I_C=2A, V_{CE}=2V^*$ $I_C=4A, V_{CE}=2V^*$ $I_C=10A, V_{CE}=2V^*$
Transition Frequency	f_T		130		MHz	$I_C=100mA, V_{CE}=10V$ $f=50MHz$
Output Capacitance	C_{obo}		35		pF	$V_{CB}=10V, f=1MHz$
Switching Times	t_{on} t_{off}		50 1650		ns	$I_C=1A, V_{CE}=10V$ $I_B=I_{B2}=100mA,$

*Measured under pulsed conditions. Pulse width=300 μ s. Duty cycle $\leq$ 2%
Spice parameter data is available upon request for this device

TYPICAL CHARACTERISTICS



ELECTRICAL CHARACTERISTICS $T_{amb} = 25^{\circ}C$ (atunless otherwise stated)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	200	300		V	$I_C=100\mu A$
Collector-Emitter Breakdown Voltage	$V_{(BR)CER}$	200	300		V	$I_C=1\mu A, R_B \leq 1k\Omega$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	100	120		V	$I_C=10mA^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	6	8		V	$I_E=100\mu A$
Collector Cut-Off Current	I_{CBO}			10 1	nA μA	$V_{CB}=150V, T_{amb}=25^{\circ}C$ $V_{CB}=150V$ $T_{amb}=100^{\circ}C$
Collector Cut-Off Current	I_{CER} $R \leq 1k\Omega$			10 1	nA μA	$V_{CB}=150V, T_{amb}=25^{\circ}C$ $V_{CB}=150V$ $T_{amb}=100^{\circ}C$
Emitter Cut-Off Current	I_{EBO}			10	nA	$V_{EB}=6V$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		14 100	50 150 340	mV	$I_C=0.1A, I_B=5mA^*$ $I_C=2A, I_B=100mA^*$ $I_C=5A, I_B=500mA^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			1250	mV	$I_C=5A, I_B=500mA^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$			1100	mV	$I_C=5A, V_{CE}=2V^*$
Static Forward Current Transfer Ratio	h_{FE}	100 100 50 20	200 200 100 30	300		$I_C=10mA, V_{CE}=2V$ $I_C=2A, V_{CE}=2V^*$ $I_C=4A, V_{CE}=2V^*$ $I_C=10A, V_{CE}=2V^*$
Transition Frequency	f_T		130		MHz	$I_C=100mA, V_{CE}=10V$ $f=50MHz$
Output Capacitance	C_{obo}		35		pF	$V_{CB}=10V, f=1MHz$
Switching Times	t_{on} t_{off}		50 1650		ns	$I_C=1A, V_{CE}=10V$ $I_B=I_{B2}=100mA,$

*Measured under pulsed conditions. Pulse width=300 μ s. Duty cycle $\leq$ 2%
Spice parameter data is available upon request for this device

TYPICAL CHARACTERISTICS

